



## NPN BCY58 – BCY59

### SILICON PLANAR EPITAXIAL TRANSISTORS

The BCY58 and BCY59 are NPN transistors mounted in TO-18 metal package with the collector connected to the case .

They are designed for use in audio drive and low-noise input stages.  
Compliance to RoHS.

#### ABSOLUTE MAXIMUM RATINGS

Symbol	Ratings		Value	Unit
$V_{CEO}$	Collector-Emitter Voltage(1)	<b>BCY59</b>	45	V
		<b>BCY58</b>	32	
$V_{CES}$	Collector-Emitter Voltage ( $V_{BE} = 0$ )	<b>BCY59</b>	45	V
		<b>BCY58</b>	32	
$V_{EBO}$	Emitter-Base Voltage	<b>BCY59</b>	7	V
		<b>BCY58</b>	7	
$I_C$	Collector Current	<b>BCY59</b>	200	mA
		<b>BCY58</b>		
$I_B$	Base Current	<b>BCY59</b>	50	mA
		<b>BCY58</b>		
$P_D$	Total Power Dissipation @ $T_{amb} = 45^\circ$	<b>BCY59</b>	0.39	mW
		<b>BCY58</b>		
$P_D$	Total Power Dissipation @ $T_{case} = 45^\circ$	<b>BCY59</b>	1	Watts
		<b>BCY58</b>		
$T_J$	Junction Temperature	<b>BCY59</b>	200	°C
		<b>BCY58</b>		
$T_{Stg}$	Storage Temperature range	<b>BCY59</b>	-65 to +150	°C
		<b>BCY58</b>		

(1) Applicable up to  $I_C = 500\text{mA}$

#### THERMAL CHARACTERISTICS

Symbol	Ratings		Value	Unit
$R_{thJ-a}$	Thermal Resistance, Junction to mounting base	<b>BCY59</b>	450	°C/W
		<b>BCY58</b>		
$R_{thJ-c}$	Thermal Resistance, Junction to ambient in free air	<b>BCY59</b>	150	°C/W
		<b>BCY58</b>		



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### ELECTRICAL CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

Symbol	Ratings	Test Condition(s)	Min	Typ	Mx	Unit	
I <sub>CES</sub>	Collector Cutoff Current	V <sub>CB</sub> =45 V, V <sub>BE</sub> =0V V <sub>CB</sub> =32 V, V <sub>B</sub> =0V	<b>BCY59</b> <b>BCY58</b>	-	-	10	nA
I <sub>CES</sub>	Collector Cutoff Current	V <sub>CB</sub> =45 V V <sub>BE</sub> =0V, T <sub>amb</sub> =150°C V <sub>CB</sub> =32 V V <sub>BE</sub> =0V, T <sub>amb</sub> =150°C	<b>BCY59</b> <b>BCY58</b>	-	-	10	µA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>BE</sub> =5.0 V, I <sub>C</sub> =0	<b>BCY59</b> <b>BCY58</b>	-	-	10	nA
V <sub>CEO</sub>	Collector Emitter Breakdown Voltage	I <sub>C</sub> =2 mA, I <sub>B</sub> =0	<b>BCY59</b> <b>BCY58</b>	45 32	-	-	V
V <sub>EBO</sub>	Emitter Base Breakdown Voltage	I <sub>E</sub> =1 µA, I <sub>C</sub> =0	<b>BCY59</b> <b>BCY58</b>	7	-	-	V
V <sub>CE(SAT)</sub>	Collector-Emitter saturation Voltage	I <sub>C</sub> =10 mA, I <sub>B</sub> =0.25 mA I <sub>C</sub> =100 mA, I <sub>B</sub> =2.5 mA	<b>BCY59</b> <b>BCY58</b> <b>BCY59</b> <b>BCY58</b>	- - 0.12 0.04	0.25 0.08		V
V <sub>BE(SAT)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> =10 mA, I <sub>B</sub> =0.25 mA I <sub>C</sub> =100 mA, I <sub>B</sub> =2.5 mA	<b>BCY59</b> <b>BCY58</b> <b>BCY59</b> <b>BCY58</b>	0.6 0.7	0.85		
V <sub>BE</sub>	Base-Emitter Voltage	I <sub>C</sub> =10 µA, V <sub>CE</sub> =5 V I <sub>C</sub> =20 µA, V <sub>CE</sub> =V <sub>CE</sub> max T <sub>j</sub> =100°C I <sub>C</sub> =2 mA, V <sub>CE</sub> =5 V I <sub>C</sub> =10 mA, V <sub>CE</sub> =1 V I <sub>C</sub> =100 mA, V <sub>CE</sub> =1 V	<b>BCY59</b> <b>BCY58</b> <b>BCY59</b> <b>BCY58</b> <b>BCY59</b> <b>BCY58</b> <b>BCY59</b> <b>BCY58</b>	- 0.2 0.55 - -	0.5 - - 0.7 0.76	- - 0.7 -	V

			BCY59VII	BCY59VIII	BCY59IX	BCY59X
			BCY58VII	BCY58VIII	BCY58IX	BCY58X
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> =10 µA, V <sub>CE</sub> =5 V	- Typ.20	>20 Typ.95	>40 Typ.190	>60 Typ.300
		I <sub>C</sub> =10 µA, V <sub>CE</sub> =5 V	>120	>180	>250	>380
		I <sub>C</sub> =10 µA, V <sub>CE</sub> =5 V	<220	<310	<460	<630
		I <sub>C</sub> =10 mA, V <sub>CE</sub> =1 V	>80	>120	>160	>240
		I <sub>C</sub> =100 mA, V <sub>CE</sub> =1 V	- >40	<400 >45	<630 >60	<1000 >60
h <sub>fe</sub>	Small-Signal Current Gain	I <sub>C</sub> =2 mA, V <sub>CE</sub> =5 V, f=1kHz	>125 <250	>175 <350	>250 <500	>350 <700



## NPN BCY58 – BCY59

Symbol	Ratings	Test Condition(s)	Min	Typ	Mx	Unit	
$f_T$	Transition frequency	$I_C = 10 \text{ mA}, V_{CE} = 5 \text{ V}$ $f = 100 \text{ MHz}$	<b>BCY59</b> <b>BCY58</b>	150	-	-	MHz
$F$	Noise figure , $RS = 2k\Omega$	$I_C = 200 \mu\text{A}, V_{CE} = 5 \text{ V}$ $f = 1 \text{ kHz}, B = 200 \text{ Hz}$	<b>BCY59</b> <b>BCY58</b>	-	2	6	db
$t_d$	Delay time		<b>BCY59</b> <b>BCY58</b>	-	35	-	
$t_r$	Rise time		<b>BCY59</b> <b>BCY58</b>	-	50	-	
$t_{on}$	Turn on time	$I_C = 10 \text{ mA}, I_B = 1 \text{ mA}$ $-I_{BM} = 1 \text{ mA}, V_{BB} = 3.6 \text{ V}$	<b>BCY59</b> <b>BCY58</b>	-	85	150	ns
$t_s$	Storage time	$R1 = R2 = 5k\Omega$ $R_L = 990 \Omega$	<b>BCY59</b> <b>BCY58</b>	-	400	-	
$t_f$	Fall time		<b>BCY59</b> <b>BCY58</b>	-	80	-	
$t_{off}$	Turn off time		<b>BCY59</b> <b>BCY58</b>	-	480	800	
$t_d$	Delay time		<b>BCY59</b> <b>BCY58</b>	-	5	-	
$t_r$	Rise time		<b>BCY59</b> <b>BCY58</b>	-	50	-	
$t_{on}$	Turn on time	$I_C = 100 \text{ mA}, I_B = 10 \text{ mA}$ $-I_{BM} = 10 \text{ mA}, V_{BB} = 5 \text{ V}$	<b>BCY59</b> <b>BCY58</b>	-	55	150	ns
$t_s$	Storage time	$R1 = 500\Omega, R2 = 700\Omega$ $R_L = 990 \Omega$	<b>BCY59</b> <b>BCY58</b>	-	250	-	
$t_f$	Fall time		<b>BCY59</b> <b>BCY58</b>	-	200	-	
$t_{off}$	Turn off time		<b>BCY59</b> <b>BCY58</b>	-	450	800	
$C_c$	Collector capacitance	$I_E = I_e = 0, V_{CB} = 10 \text{ V}$ $f = 1 \text{ MHz}$	<b>BCY59</b> <b>BCY58</b>	-	-	5	pF
$C_E$	Emitter capacitance	$I_C = I_e = 0, V_{EB} = 0.5 \text{ V}$ $f = 1 \text{ MHz}$	<b>BCY59</b> <b>BCY58</b>	-	-	15	pF

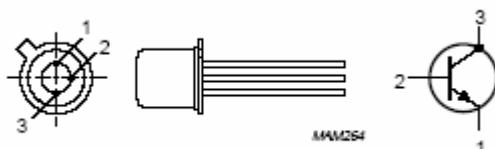
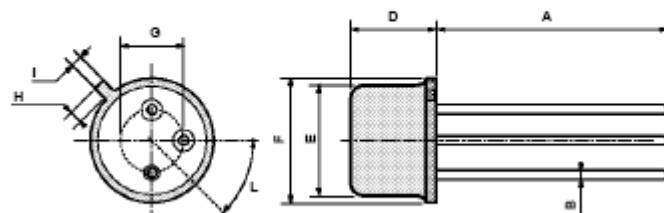


## NPN BCY58 – BCY59

### MECHANICAL DATA CASE TO-18

DIMENSIONS		
	mm	inches
A	12,7	0,5
B	0,49	0,019
D	5,3	0,208
E	4,9	0,193
F	5,8	0,228
G	2,54	0,1
H	1,2	0,047
I	1,16	0,045
L	45°	45°

Pin 1 :	emitter
Pin 2 :	base
Pin 3 :	Collector



Information furnished is believed to be accurate and reliable. However, CS assumes no responsibility for the consequences of use of such information nor for errors that could appear.

Data are subject to change without notice.